



FQA90N15

N-Channel QFET® MOSFET 150 V, 90 A, 18 mΩ

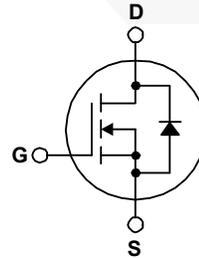
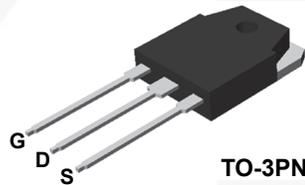
Features

- $R_{DS(on)} = 18\text{ m}\Omega$ (Max.) @ $V_{GS} = 10\text{ V}$, $I_D = 45\text{ A}$
- Low Gate Charge (Typ. 220 nC)
- Low C_{rss} (Typ. 200 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | FQA90N15 | Unit |
|----------------|--|-------------|-----------|
| V_{DSS} | Drain-Source Voltage | 150 | V |
| I_D | Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$) | 90 63.5 | A A |
| I_{DM} | Drain Current - Pulsed (Note 1) | 360 | A |
| V_{GSS} | Gate-Source voltage | ± 25 | V |
| E_{AS} | Single Pulsed Avalanche Energy (Note 2) | 1400 | mJ |
| I_{AR} | Avalanche Current (Note 1) | 90 | A |
| E_{AR} | Repetitive Avalanche Energy (Note 1) | 37.5 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 6.0 | V/ns |
| P_D | Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate Above 25°C | 375 2.5 | W W/°C |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +175 | °C |
| T_L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | FQA90N15 | Unit |
|-----------------|---|----------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.4 | °C/W |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink, Typ. | 0.24 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 40 | °C/W |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|----------|---------|----------------|-----------|------------|----------|
| FQA90N15 | FQA90N15 | TO-3PN | Tube | N/A | N/A | 30 units |

Electrical Characteristics T_C = 25°C unless otherwise noted.

| Symbol | Parameter | Conditions | Min. | Typ. | Max | Units |
|---|---|--|----------|-------|---------|----------|
| Off Characteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0V, I _D = 250μA | 150 | -- | -- | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 250μA, Referenced to 25°C | -- | 0.15 | -- | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 150V, V _{GS} = 0V V _{DS} = 120V, T _C = 150°C | -- | -- | 1 10 | μA μA |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 25V, V _{DS} = 0V | -- | -- | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -25V, V _{DS} = 0V | -- | -- | -100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 2.0 | -- | 4.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10V, I _D = 45A | -- | 0.014 | 0.018 | Ω |
| g _{FS} | Forward Transconductance | V _{DS} = 40V, I _D = 45A | -- | 68 | -- | S |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz | -- | 6700 | 8700 | pF |
| C _{oss} | Output Capacitance | | -- | 1400 | 1800 | pF |
| C _{rss} | Reverse Transfer Capacitance | | -- | 200 | 260 | pF |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 75V, I _D = 90A R _G = 25Ω | -- | 105 | 220 | ns |
| t _r | Turn-On Rise Time | | -- | 760 | 1500 | ns |
| t _{d(off)} | Turn-Off Delay Time | | -- | 470 | 950 | ns |
| t _f | Turn-Off Fall Time | | (Note 4) | -- | 410 | 830 |
| Q _g | Total Gate Charge | V _{DS} = 120V, I _D = 90A V _{GS} = 10V | -- | 220 | 285 | nC |
| Q _{gs} | Gate-Source Charge | | -- | 43 | -- | nC |
| Q _{gd} | Gate-Drain Charge | | (Note 4) | -- | 110 | -- |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | -- | -- | 90 | A |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | -- | -- | 360 | A |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0V, I _S = 90A | -- | -- | 1.5 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0V, I _S = 90A di/dt = 100A/μs | -- | 175 | -- | ns |
| Q _{rr} | Reverse Recovery Charge | | -- | 0.97 | -- | μC |

NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 0.29 mH, I_{AS} = 90 A, V_{DD} = 25 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 90 A, di/dt ≤ 300 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

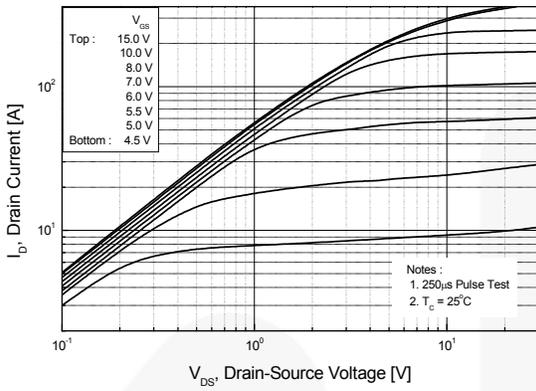


Figure 2. Transfer Characteristics

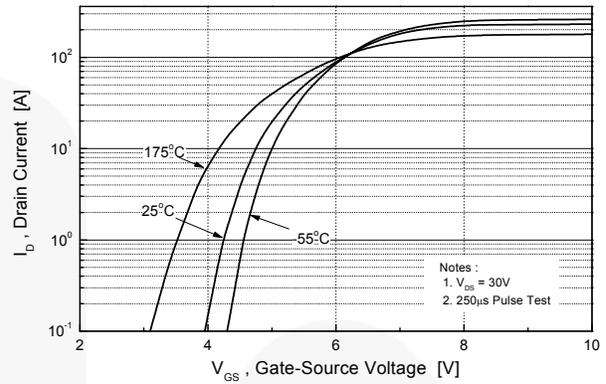


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

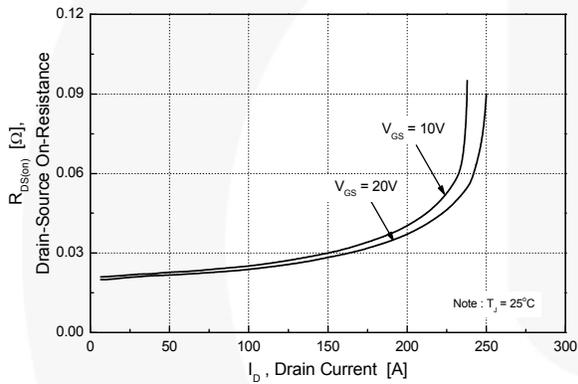


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

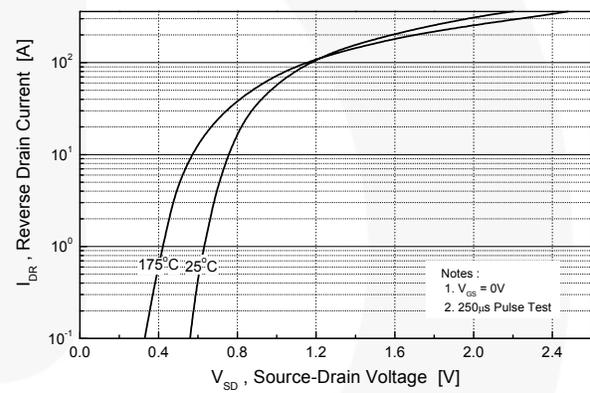


Figure 5. Capacitance Characteristics

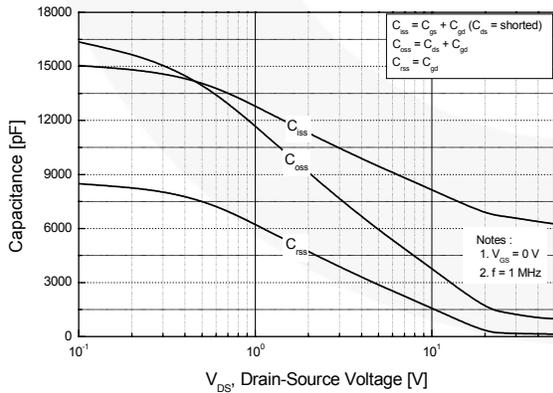
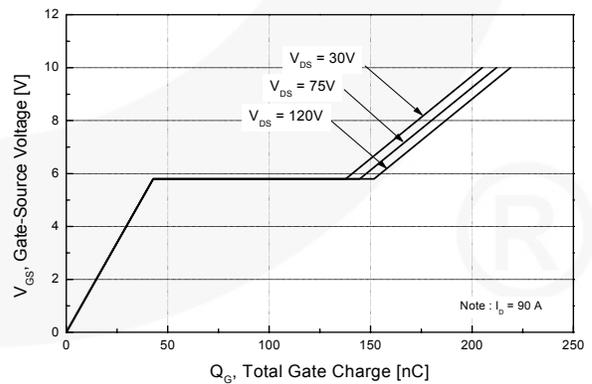


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

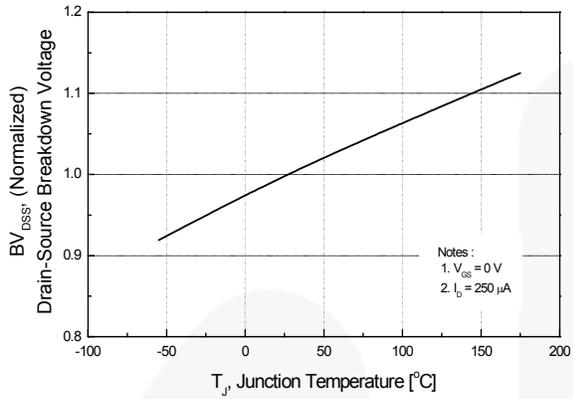


Figure 8. On-Resistance Variation vs. Temperature

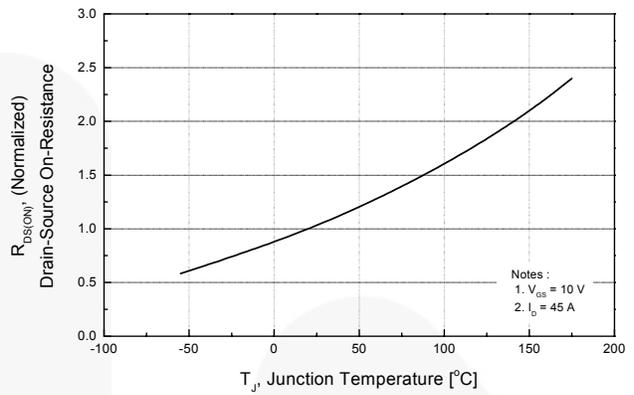


Figure 9. Maximum Safe Operating Area

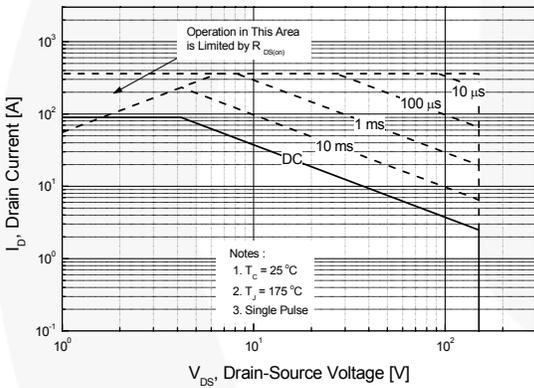


Figure 10. Maximum Drain Current vs. Case Temperature

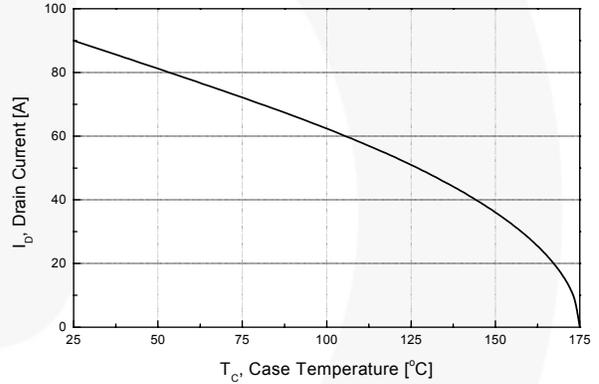
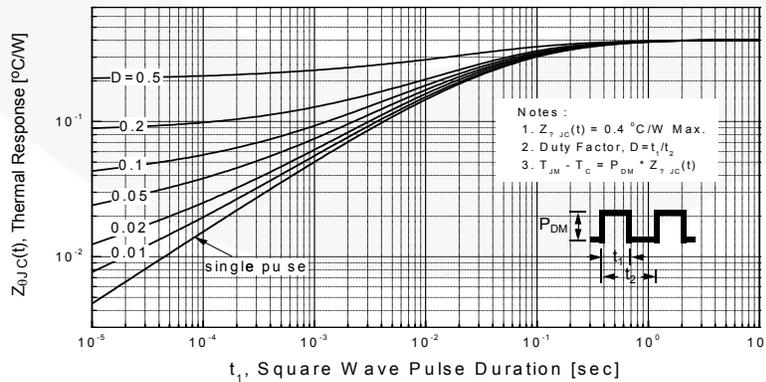


Figure 11. Transient Thermal Response Curve



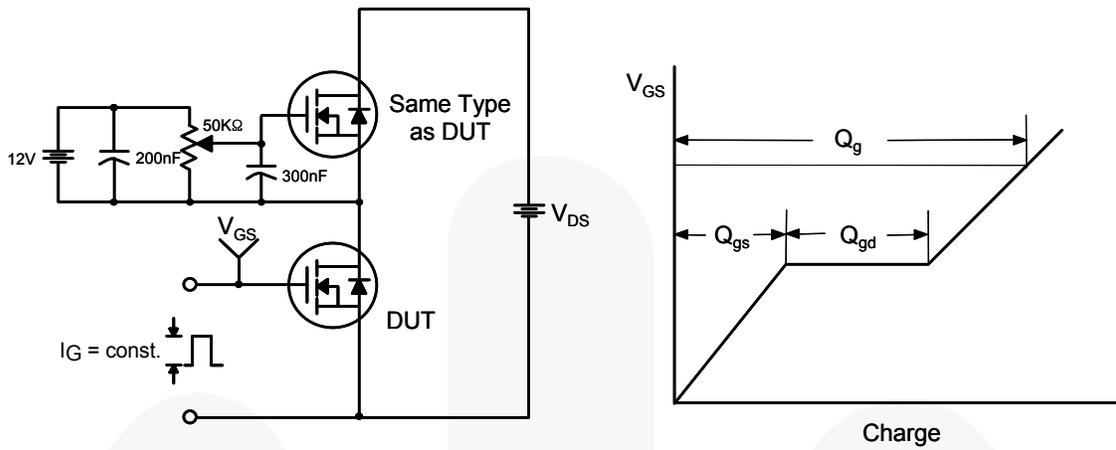


Figure 12. Gate Charge Test Circuit & Waveform

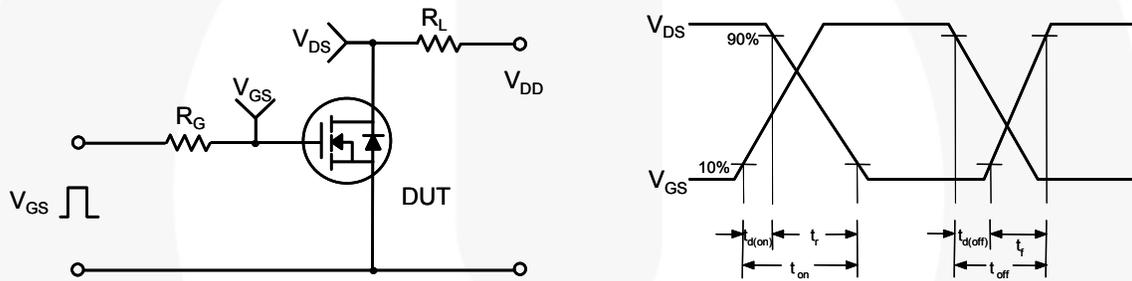


Figure 13. Resistive Switching Test Circuit & Waveforms

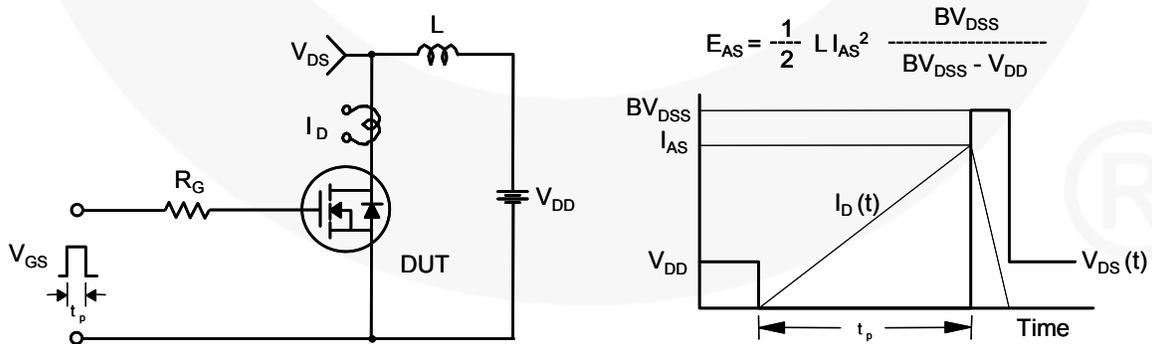


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

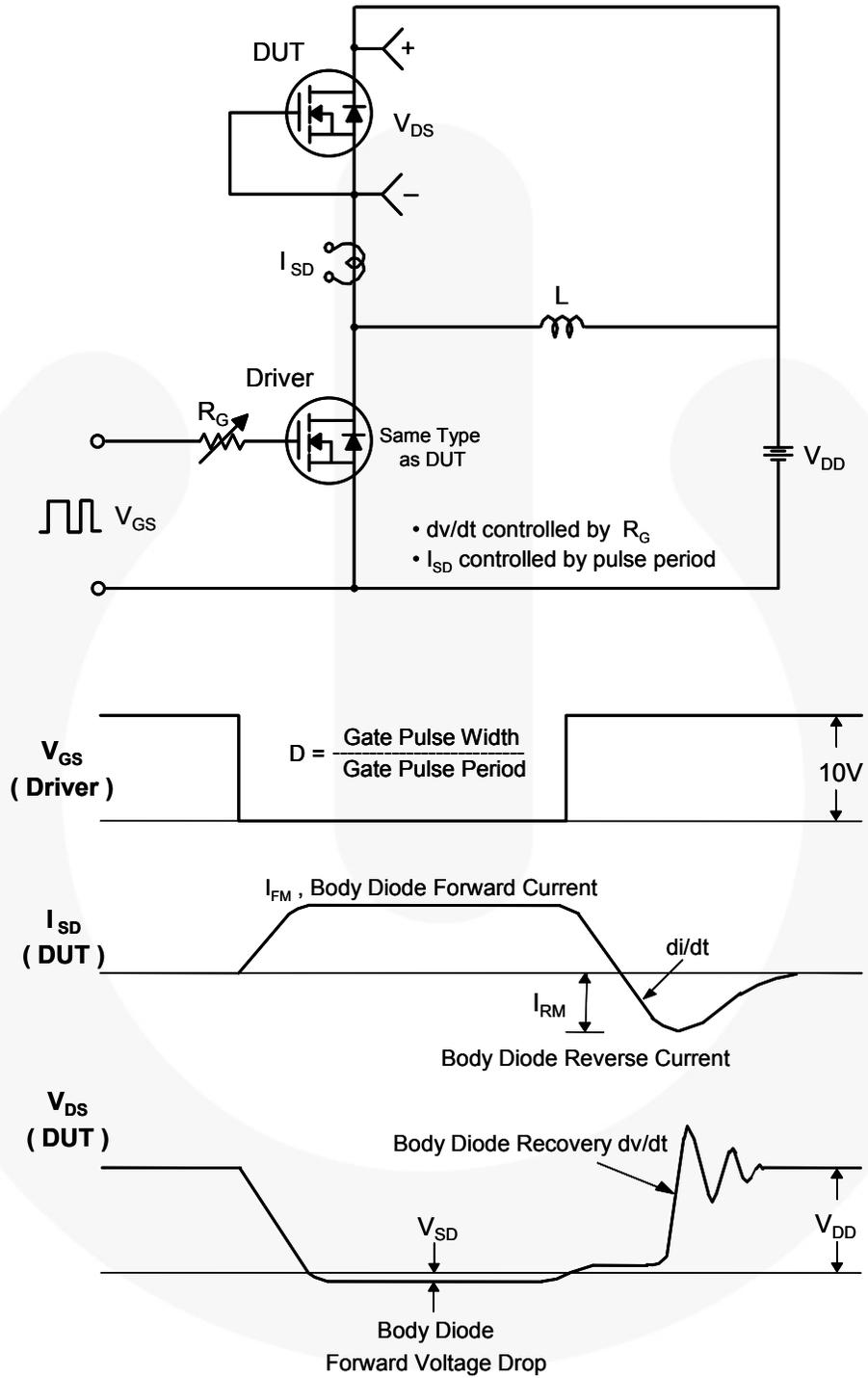
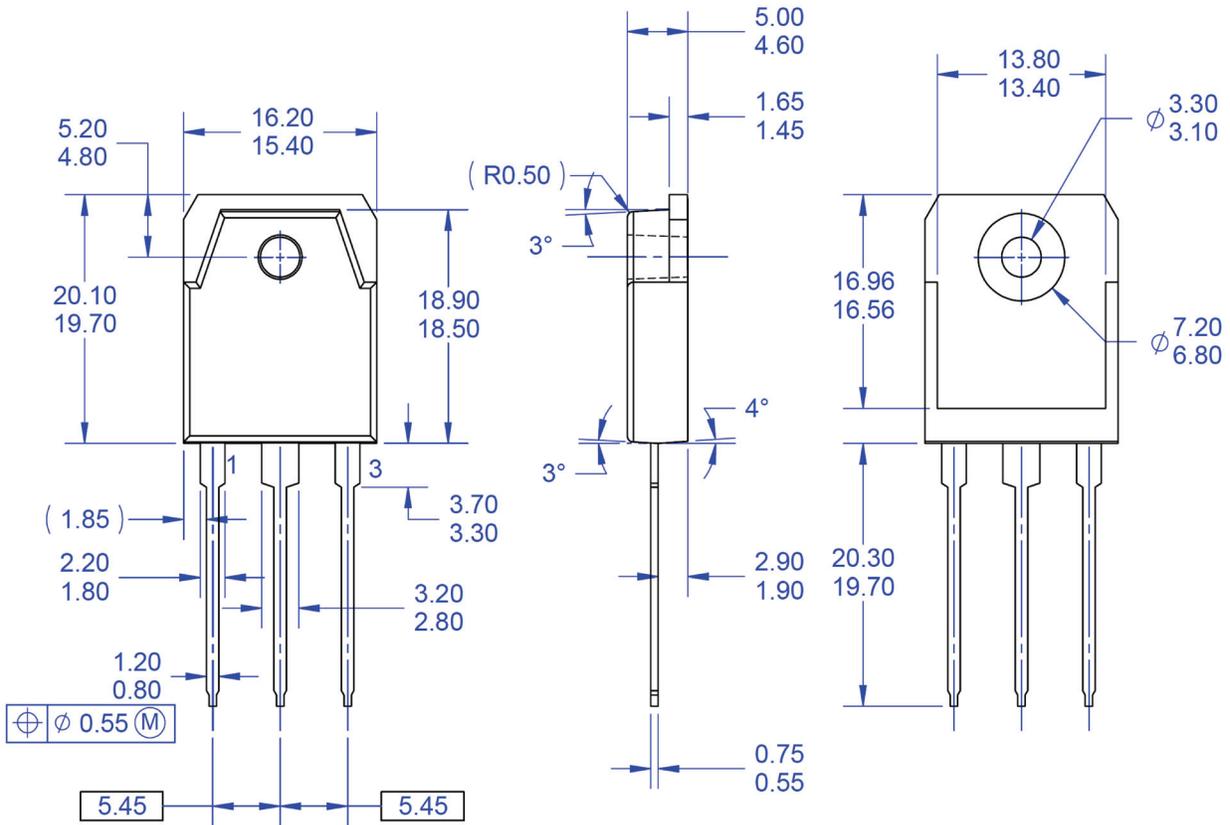


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- E) DRAWING FILE NAME: TO3PN03AREV1.
- F) FAIRCHILD SEMICONDUCTOR.

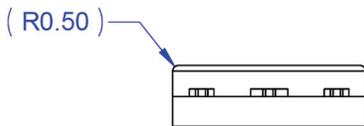


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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